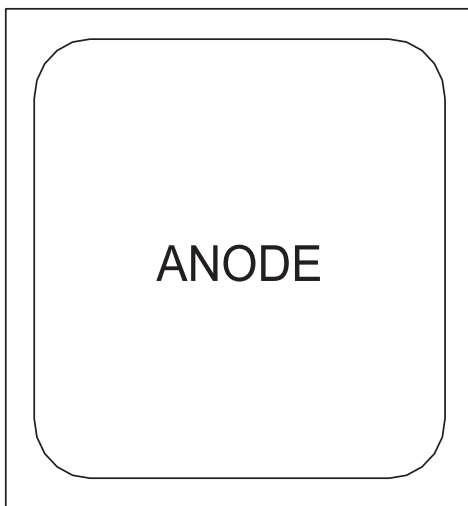


**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	98 x 98 MILS
Die Thickness	10.6 MILS
Anode Bonding Pad Area	82.5 x 82.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

**GEOMETRY**



BACKSIDE CATHODE R0

**GROSS DIE PER 4 INCH WAFER**

1,170

**PRINCIPAL DEVICE TYPES**

CR6AF1GPP Series

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com

R1 (1-August 2002)

The Typical Electrical Characteristics data  
for this chip is currently being revised.

For the latest updated data for this Chip Process,  
please visit our website at:

[www.centrasemi.com/chip](http://www.centrasemi.com/chip)

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